

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

1-3. (Cancelled)

4. (Previously Presented) A method of passivating a conductive material, comprising:

providing said conductive material, wherein said conductive material has an ability to associate with oxygen; and  
exposing said conductive material to methylsilane.

5-75. (Cancelled)

76. (Previously Presented) A method of passivating a conductive layer, comprising:

providing a tungsten nitride layer;  
providing a polysilicon layer on the tungsten nitride layer; and  
exposing the tungsten nitride layer to methylsilane.

77. (Previously Presented) The method in claim 76, wherein exposing the tungsten nitride layer comprises exposing the tungsten nitride layer to at least one material in the recited group under process conditions comprising:

a flow rate of the material of about 2 sccm to about 400 sccm;  
a flow rate of about 50 sccm to about 100 sccm for an inert carrier gas;  
a temperature ranging from about 150 to about 600 degrees Celsius;  
a pressure ranging from about 50 millitorr to about 760 torr; and

a process time ranging from about 50 to about 500 seconds.

78-80. (Cancelled)

81. (Previously Presented) A method of passivating a conductive layer, comprising:

providing a first conductive plug;

providing a first conductive layer on the plug;

exposing the first conductive layer to methylsilane; and

after exposing the first conductive layer, forming a second conductive layer on the first conductive layer.

82. (Previously Presented) The method of claim 81 wherein the plug comprises at least one of polysilicon, tungsten, copper, and aluminum.

83. (Previously Presented) The method of claim 81 wherein the first conductive layer comprises tungsten nitride.

84. (Previously Presented) The method of claim 81 wherein the second conductive layer comprises copper.

85. (Previously Presented) The method of claim 81 wherein exposing the first conductive layer reduces an ability of the first conductive layer to associate with oxygen.

86-88. (Cancelled)

89. (Previously Presented) The method of claim 4 wherein the conductive layer comprises at least one of tungsten nitride, polysilicon, tungsten, copper, and aluminum.

90. (Previously Presented) The method of claim 4 wherein exposing said conductive material comprises exposing the conductive material to at least one material in the recited group under process conditions comprising:

- a flow rate of the material of about 2 sccm to about 400 sccm;
- a flow rate of about 50 sccm to about 100 sccm for an inert carrier gas;
- a temperature ranging from about 150 to about 600 degrees Celsius;
- a pressure ranging from about 50 millitorr to about 760 torr; and
- a process time ranging from about 50 to about 500 seconds.

91. (Previously Presented) The method of claim 90 wherein the inert carrier gas comprises He or Ar.

92. (Previously Presented) The method of claim 77 wherein the inert carrier gas comprises He or Ar.